Vishay Semiconductors

## Hyperfast Rectifier, 15 A FRED Pt<sup>®</sup> G5



### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS									
I <sub>F(AV)</sub>	15 A								
V <sub>R</sub>	1200 V								
V <sub>F</sub> at I <sub>F</sub> at 125 °C	1.7 V								
t <sub>rr</sub>	37 ns								
T <sub>J</sub> max.	175 °C								
Package	D <sup>2</sup> PAK 2L (TO-263AB 2L)								
Circuit configuration	Single								

### **FEATURES**

- · Minimum creepage and clearance distances are 5.2 mm and 5.4 mm respectively
- Hyperfast and optimized Q<sub>rr</sub>
- HALOGEN Best in class forward voltage drop and switching FREE losses trade off
- · Optimized for high speed operation
- 175 °C maximum operating junction temperature
- · Polyimide passivation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant. Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V <sub>RRM</sub>		1200	V						
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 110 °C, D = 0.50	15							
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 110 °C, D = 0.50, f = 20 kHz	30	А						
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_{C}$ = 45 °C, $t_{p}$ = 10 ms, sine wave	125							
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C						

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	1200	-	-					
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15 A	-	1.9	2.5	V				
		I <sub>F</sub> = 15 A, T <sub>J</sub> = 125 °C	-	1.7	-					
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	50					
Reverse leakage current	I <sub>R</sub>	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	10	-	pF				
Series inductance	L <sub>S</sub>	Measured to lead 5 mm from package body	-	8	-	nH				

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COMPLIANT







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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{c}$	It = 100 A/ $\mu$ s, V <sub>R</sub> = 30 V	-	37	-				
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	95	-	ns			
		T <sub>J</sub> = 125 °C		-	146	-	115			
Peak recovery current	I	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 10 A dI <sub>F</sub> /dt = 600 A/μs	-	14	-	A			
Fear recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm R} = 400 \text{ V}$	-	19	-				
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	545	-	nC			
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	1200	-				
Reverse recovery time	+	T <sub>J</sub> = 25 °C		-	75.5	-	ns			
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	100	-	115			
Deals receivers ourrent	1	T <sub>J</sub> = 25 °C	l <sub>F</sub> = 15 A dl <sub>F</sub> /dt = 1000 A/µs	-	23	-	A			
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm R} = 800 \text{ V}$	-	35	-				
Beveree receiver charge	0	T <sub>J</sub> = 25 °C		-	935	-				
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	1985	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	1.7	°C/W				
Weight			-	2.0	-	g				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C				
Marking device		Case style D <sup>2</sup> PAK 2L (TO-263AB 2L)		E5TH1	512SH					

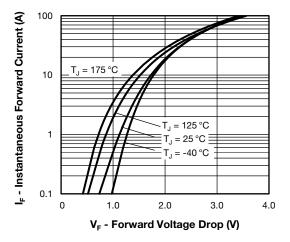


Fig. 1 - Forward Voltage Drop Characteristics

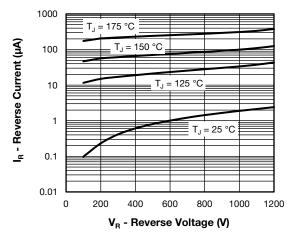
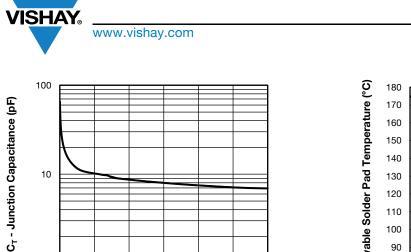


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



## 200 400 600 800 1000 1200 V<sub>R</sub> - Reverse Voltage (V)

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

10

1

0

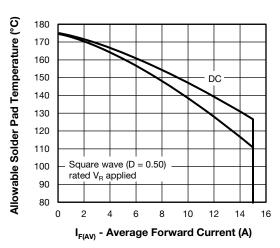


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

**VS-E5TH1512S2LHM3** 

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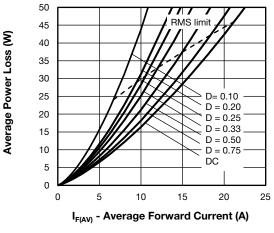


Fig. 5 - Forward Power Loss Characteristics

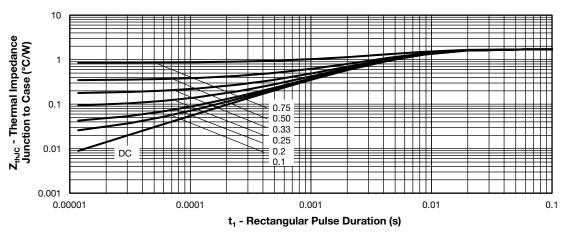


Fig. 6 - Transient Thermal Impedance, Junction to Case

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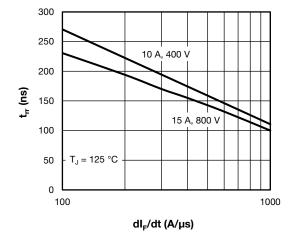
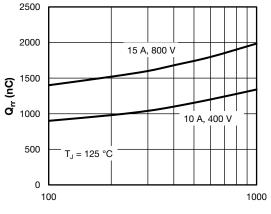


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt



 $dI_F/dt$  (A/µs) Fig. 8 - Typical Stored Charge vs.  $dI_F/dt$ 

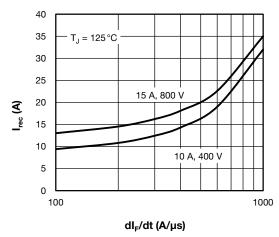


Fig. 9 - Typical Stored Charge vs. dl<sub>F</sub>/dt



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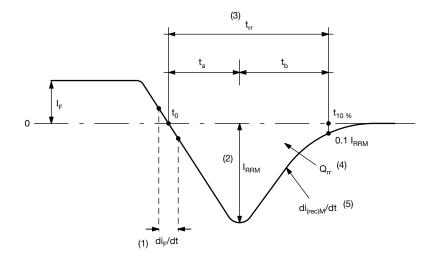


Fig. 10 - Reverse Recovery Waveform and Definitions

#### Notes

- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- $^{(3)}$  t<sub>rr</sub> reverse recovery time measured from t<sub>0</sub>, crossing point of negative going I<sub>F</sub>, to point t<sub>10%</sub>, 0.1 I<sub>RRM</sub>
- $^{(4)}~~\text{Q}_{rr}$  area under curve defined by  $t_0$  and  $t_{10}~\%$

$$Q_{rr} = \int_{t_0}^{t_{10}\%} I(t)dt$$

 $^{(5)}$  di<sub>(rec)</sub>M/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

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Device code	VS-	Е	5	т	н	15	12	S2	L	н	М3
	1	2	3	4	5	6	7	8	9	10	(11)
	1 -	· Visł	nay Sem	niconduo	ctors pro	oduct					
	2 -	E=	single c	liode							
	3 -	· 5 =	FRED g	eneratio	on 5						
	<ul> <li>Package:</li> <li>T = D<sup>2</sup>PAK 2L (TO-263AB 2L) package</li> </ul>										
	5 -	• H=	hyperfa	ast recov	very						
	6 -	- Cur	rent rati	ng (15 =	= 15 A)						
	7 -	Vol	tage rati	ng (12 =	= 1200 \	/)					
	8 -	· S2	= true 2	pin D <sup>2</sup> F	PAK						
	<ul> <li>9 - None = tube (50 pieces)</li> <li>• L = tape and reel (left oriented, for D<sup>2</sup>PAK package) If needed different orientation/packaging, please contact factory</li> </ul>										,
	10 -		AEC-Q								
	11 -		rironmer = halog	-		complia	ant, and	termina	ation lea	ıd (Pb)-1	ree

ORDERING INFORMATION (Example)								
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION						
VS-E5TH1512S2LHM3	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96683						
Part marking information	www.vishay.com/doc?96693						
Packaging information	www.vishay.com/doc?95032						

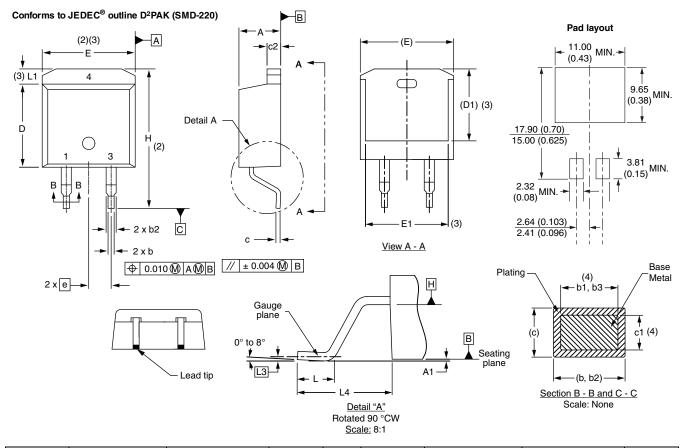


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D<sup>2</sup>PAK 2L (TO-263AB 2L)

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL		MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25	BSC	0.010	BSC	
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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